1N914 THRU 1N4454

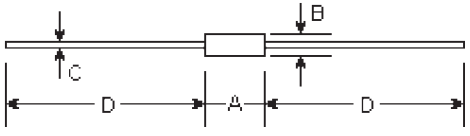
SILICON EPITAXIAL PLANAR DIODES

Features

Silicon Epitaxial Planar Diodes
for general purpose and switching

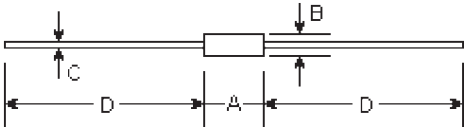
The types 1N4149, 1N4447 and 1N4449 are also available in glass case DO-34.

DO-34



DIMENSIONS					
DIM	inches		mm		Note
	Min.	Max.	Min.	Max.	
A	-	0.114	-	2.9	
B	-	0.075	-	1.9	ф
C	-	0.017	-	0.42	ф
D	0.630	-	16.0	-	

DO-35



DIMENSIONS					
DIM	inches		mm		Note
	Min.	Max.	Min.	Max.	
A	-	0.154	-	3.9	
B	-	0.075	-	1.9	ф
C	-	0.020	-	0.52	ф
D	1.083	-	27.50	-	

Electrical Characteristics

Type	Peak reverse voltage	Max. aver. rectified current	Max. power dissip. at 25℃	Max. junction temper-ature	Max. forward voltage drop		Max. reverse current		Max. reverse recovery time	
	V_{RM} V	I_O mA	P_{tot} mW	T_j ℃	V_F V	at I_F mA	I_n nA	at V_R V	t_{rr} nS	Conditions
1N914	100	75	500	200	1.0	10	25	20	Max. 4.0	I_F=10mA, V_R=6V, R_L=100Ω, to I_R=1mA
1N4149 [1]	100	150	500	200	1.0	10	25	20	Max. 4.0	I_F=10mA, V_R=6V, R_L=100Ω, to I_R=1mA
1N4150	50	200	500	200	1.0	200	100	50	Max. 4.0	I_F=I_R=10 to 200 mA, to 0.1 I_F
1N4152	40	150	400	175	0.55	0.10	50	30	Max. 2.0	I_F=10mA, V_R=6V, R_L=100Ω, to I_R=1mA
1N4153	75	150	400	175	0.55	0.10	50	50	Max. 2.0	I_F=10mA, V_R=6V, R_L=100Ω, to I_R=1mA
1N4154	35	150 [2]	500	200	1.0	0.10	100	25	Max. 2.0	I_F=10mA, V_R=6V, R_L=100Ω, to I_R=1mA
1N4447 [1]	100	150	500	200	1.0	20	25	20	Max. 4.0	I_F=10mA, V_R=6V, R_L=100Ω, to I_R=1mA
1N4449 [1]	100	150	500	200	1.0	30	25	20	Max. 4.0	I_F=10mA, V_R=6V, R_L=100Ω, to I_R=1mA
1N4450	40	150	400	175	0.54	0.50	50	30	Max. 4.0	I_F=I_R=10mA, to I_R=1mA
1N4451	40	150	400	175	0.50	0.10	50	30	Max. 10	I_F=I_R=10mA, to I_R=1mA
1N4453	30	150	400	175	0.55	0.01	50	20	-	-
1N4454	75	150	400	175	1.0	10	100	50	Max. 4.0	I_F=I_R=10mA, to I_R=1mA

Notes:

(1) These diodes are also avaiable in glass case DO-34

(2) Valid provided that leads at a distance of 8 mm from case are kept at ambient temperature

Parameters for diodes in case DO-34: P_{tot}=300mW T_S=-65 to +175℃

T_J=175℃ $R_{tha} \leqslant$ 0.4K/mW